In the claims:

1. (previously presented) A method of fabricating MOSFET transistors in a semiconductor device, comprising the steps of:

providing a semiconductor device substrate;

implanting a first transistor region associated with a first transistor device in the semiconductor device substrate to adjust a threshold voltage associated with the first transistor device and concurrently implanting a portion of a second transistor region in the semiconductor device substrate associated with a second transistor device in the semiconductor device to form source/drain regions associated with the second transistor device with a channel region between said source/drain regions;

then forming a first gate oxide structure overlying a channel region in the first transistor region, the first gate oxide structure having a first thickness and forming a second gate oxide structure overlying the channel region in the second transistor region, the second gate oxide structure having a second thickness, the second thickness being greater than the first thickness.

2. (previously presented) The method of claim 1, further comprising the step of then implanting a portion of the first transistor region to form source/drain regions associated with the first transistor device.

3. (previously presented) The method of claim 2, further comprising the steps of then implanting a third transistor region associated with a third transistor device in the semiconductor device using a third implantation process to adjust a threshold voltage associated with the third transistor device and concurrently implanting a portion of a fourth transistor region in the semiconductor device substrate associated with a fourth transistor device in the semiconductor device to form source/drain regions associated with the fourth transistor device with a channel region between said source/drain regions;

then forming a third gate oxide structure overlying a channel region in the third transistor region, the third gate oxide structure having a third thickness and forming a fourth gate oxide structure overlying the channel region in the fourth transistor region, the fourth gate oxide structure having a fourth thickness, the fourth thickness being greater than the third thickness.

4. (previously presented) The method of claim 3, further comprising the step of implanting a portion of the third transistor region to form a source/drain region associated with the third transistor device.

5. (previously presented) The method of claim 3, wherein the first and third transistor devices comprise a first one of an NMOS transistor and a PMOS transistor, and wherein the second and fourth transistor devices comprise a second one of an NMOS transistor and a PMOS transistor.

6. (previously presented) The method of claim 3, wherein the first and third transistor devices comprise NMOS transistors, wherein the second and fourth transistor devices comprise PMOS transistors, and wherein implanting the third transistor region and a portion of the fourth transistor region comprises implanting phosphorus in the third transistor region and a portion of the fourth transistor region.

7. (previously presented) The method of claim 6, wherein implanting phosphorus in the third transistor region and a portion of the fourth transistor region comprises the steps of:

performing a phosphorus threshold adjustment implantation in the third transistor region and a portion of the fourth transistor region using a dose of about 8 E11 cm^{-2} and an energy of about 20 keV; and

performing a phosphorus punch-through implantation in the third transistor region and a portion of the fourth transistor region using a dose of about 2 E12 cm^{-2} and an energy of about 70 keV.

8. (previously presented) The method of claim 4, wherein the first and third transistor devices comprise NMOS transistors, wherein the second and fourth transistor devices comprise PMOS transistors, and wherein implanting a portion of the third transistor region using the fourth implantation process comprises implanting boron in a portion of the fourth transistor region.

9. (previously presented) The method of claim 8, wherein implanting boron in a portion of the fourth transistor region comprises:

performing a boron LDD implantation in a portion of the fourth transistor region using a dose of about 4 E13 cm^{-2} and an energy of about 20 keV.

10. (previously presented) The method of claim 2, wherein the first transistor device comprises an NMOS transistor, wherein the second transistor device comprises a PMOS transistor, and wherein implanting a portion of the first transistor region comprises implanting at least one of phosphorus and arsenic in a portion of the first transistor region.

11. (previously presented) The method of claim 10, wherein implanting at least one of phosphorus and arsenic in a portion of the first transistor region comprises performing a phosphorus LDD implantation in a portion of the first transistor region using a dose of about 4 E13 cm^{-2} and an energy of about 40 keV.

12. (previously presented) The method of claim 1, wherein the first transistor device comprises an NMOS transistor, wherein the second transistor device comprises a PMOS transistor, and wherein implanting the first transistor region and a portion of the second transistor region comprises implanting boron in the first transistor region and a portion of the second transistor region.

13. (previously presented) The method of claim 12, wherein implanting boron in the first transistor region and a portion of the second transistor region comprises the steps of:

performing a boron threshold adjustment implantation in the first transistor region and a portion of the second transistor region using a dose of about 3 E12 cm^{-2} and an energy of about 20 keV; and

performing a boron punch-through implantation in the first transistor region and a portion of the second transistor region using a dose of about 4 E12 cm^{-2} and an energy of about 70 keV.

14. (previously presented) The method of claim 1, wherein the first thickness is about 65 Å or more and the second thickness is about 300 Å or less.

15. (previously presented) The method of claim 14, wherein the first thickness is about 75 Å and the second thickness is about 200 Å.

16. (previously presented) The method of claim 1, wherein first transistor device comprises a PMOS transistor, wherein the second transistor device comprises an NMOS transistor, and wherein implanting the first transistor region and a portion of the second transistor region comprises implanting phosphorus in the first transistor region and a portion of the second transistor region.

17. (previously presented) The method of claim 16, wherein implanting phosphorus in the first transistor region and a portion of the second transistor region comprises the steps of:

performing a phosphorus threshold adjustment implantation in the first transistor region and a portion of the second transistor region using a dose of about 8 E11 cm^{-2} and an energy of about 20 keV; and

performing a phosphorus punch-through implantation in the first transistor region and a portion of the second transistor region using a dose of about 2 E12 cm^{-2} and an energy of about 70 keV.

18. (currently amended) A method of fabricating MOSFET transistors in a semiconductor device, comprising the steps of:

providing a semiconductor substrate;

adjusting ~~a~~ the threshold voltage of a first transistor relatively low voltage device in a first region of said semiconductor device substrate; and

concurrently with said step of adjusting, forming a source/drain region of a second transistor relatively high voltage device, both using the same implant.

19. (previously presented) The method of claim 18, further comprising the step of forming a source/drain region of the first transistor device.

20. (currently amended) A method of fabricating MOSFET transistors in a semiconductor device, comprising the steps of:

providing a semiconductor substrate;

adjusting a threshold voltage of a first transistor relatively low voltage device in a first region of said semiconductor device substrate;

concurrently with said step of adjusting, forming a source/drain region of a second transistor relatively high voltage device, both using the same implant;

forming a source/drain region of the first transistor device;

~~The method of claim 19, further comprising the steps of:~~

then forming a first gate oxide structure of the first transistor device having a first thickness; and

forming a second gate oxide structure of the second transistor device having a second thickness, the second thickness being greater than the first thickness.

21. (currently amended) A method of fabricating MOSFET transistors in a semiconductor device, comprising the steps of:

providing a semiconductor substrate;

adjusting a threshold voltage of a first transistor relatively low voltage device in a first region of said semiconductor device substrate;

concurrently with said step of adjusting, forming a source/drain region of a second transistor relatively high voltage device, both using the same implant;

forming a source/drain region of the first transistor device; and

~~The method of claim 19, further comprising the steps of~~ then adjusting a threshold voltage of a third transistor device and forming a source/drain region of a fourth transistor device.

22. (previously presented) The method of claim 21, further comprising the steps of forming a source/drain region of the third transistor device.

23. (previously presented) The method of claim 22, wherein the first and third transistor devices comprise a first one of NMOS transistors and PMOS transistors, and wherein the second and fourth transistors comprise a second one of NMOS transistors and PMOS transistors.

24. (currently amended) A method of fabricating MOSFET transistors in a semiconductor device, comprising the steps of:

providing a semiconductor substrate;

adjusting a threshold voltage of a first transistor relatively low voltage device in a first region of said semiconductor device substrate; and

concurrently with said step of adjusting, forming a source/drain region of a second transistor relatively high voltage device, both using the same implant;

~~The method of claim 18~~ wherein the first transistor device comprises an NMOS transistor, wherein the second transistor device comprises a PMOS transistor, and wherein adjusting a threshold voltage of the first transistor device and forming a source/drain region of the second transistor device [using the first threshold adjust implantation process] comprises selectively implanting a first transistor region associated with the first transistor device to adjust a threshold voltage associated with the first transistor device, and implanting a portion of a second transistor region associated with the second transistor device to form a source/drain region associated with the second transistor device using boron.

25. (currently amended) A method of fabricating MOSFET transistors in a semiconductor device, comprising the steps of:

providing a semiconductor substrate;

adjusting a threshold voltage of a first transistor relatively low voltage device in a first region of said semiconductor device substrate; and

concurrently with said step of adjusting, forming a source/drain region of a second transistor relatively high voltage device, both using the same implant;

~~The method of claim 18~~ wherein the first transistor device comprises a PMOS transistor, wherein the second transistor device comprises an NMOS transistor, and wherein adjusting a threshold voltage of the first transistor device and forming a source/drain region of the second transistor device comprises selectively implanting a first transistor region associated with the first transistor device to adjust a threshold voltage associated with the first transistor device, and implanting a portion of a second transistor region associated with the second transistor device to form a source/drain region associated with the second transistor device using phosphorus.

26. (currently amended) A method of forming a source/drain region in a semiconductor device, comprising the steps of:

providing a semiconductor device substrate; and

selectively concurrently implanting a first relatively low voltage transistor region in said semiconductor device substrate to adjust ~~a~~ the threshold voltage associated with a first transistor device and implanting a portion of a second transistor region to form a source/drain region associated with a second relatively high voltage transistor device.

27. (previously presented) The method of claim 26, wherein selectively implanting the first transistor region and a portion of the second transistor region comprises the step of implanting one of phosphorus, arsenic and boron in the first transistor region and a portion of the second transistor region.

28. (previously presented) A method of fabricating a semiconductor device, comprising the steps of

providing a semiconductor device substrate;

concurrently implanting in said semiconductor device substrate an active region of a low voltage NMOS device and source/drain regions of a high voltage PMOS device using a boron threshold voltage adjust implantation;

implanting an active region of a low voltage PMOS device and source/drain regions of a high voltage NMOS device using a phosphorus threshold voltage adjust implantation process;

forming polysilicon gate structures associated with the high and low voltage NMOS and PMOS devices;

implanting source/drain regions associated with the low voltage NMOS device using a phosphorus or arsenic LDD implantation; and

implanting source/drain regions associated with the low voltage PMOS device using a boron LDD implantation.

29. (previously presented) The method of claim 28, further comprising the steps of:

forming sidewall spacers on opposite sides of the polysilicon gate structures;

further implanting the source/drain regions associated with the low and high voltage NMOS devices using a phosphorus or arsenic implantation; and

further implanting the source/drain regions associated with the low and high voltage PMOS devices using a boron implantation.

30. (previously presented) The method of claim 29, further comprising the steps of:

forming a first gate oxide layer having a first thickness overlying the active regions associated with the low voltage NMOS and PMOS devices; and

forming a second gate oxide layer having a second thickness overlying the active regions associated with high voltage NMOS and PMOS devices, wherein the second thickness is greater than the first thickness.